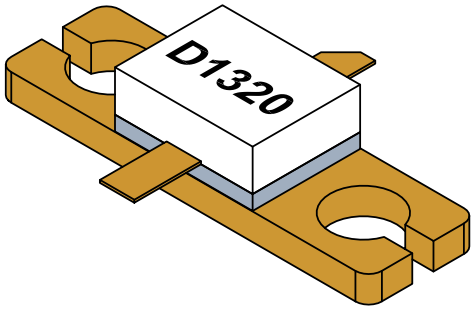
1. Description

- The D1320 is a 30W (P_{SAT}) wideband pre-matched gallium nitride (GaN) high electron mobility transistor (HEMT) with first generation RF GaN technology from Raytron.
- The D1320 operates from 3.0 to 4.5GHz with a 28V supply rail. The device is offered in an industry standard air cavity package.



D1320-PDS-F01

Figure 1. D1320 Package Outline

2. Applications

- Military and Civilian Radar
- Land Mobile and Military Radio Communications
- Avionics and Test Instrumentation

3. Features[1]

- Operating Frequency: 3.0–4.5GHz
- Output Power (P_{SAT}): 45.1dBm (32W)
- Linear Gain: 15.4dB
- Typical DE @P_{SAT}: 61.0%
- Operating Voltage: 28V
- CW and Pulse Capable
- Package Type: 200F-A

[1] Measured in Raytron DEMO @3.5GHz

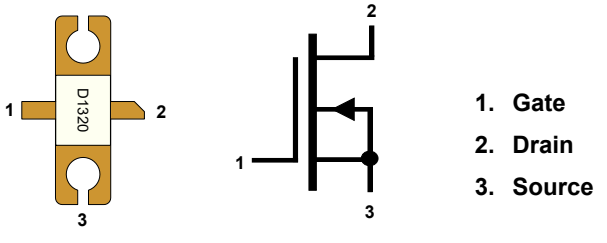
4. Brief Typical Performance

Table 1. Brief Typical Performance

Parameter	3.4GHz	3.5GHz	3.6GHz	3.7GHz	Units
Linear Gain	15.0	15.4	15.8	16.1	dB
Power Gain	12.1	12.3	12.5	12.8	dB
Drain Efficiency	65.0	61.0	61.0	62.0	%
Output Power	45.5	45.1	45.2	44.9	dBm
Output Power	35	32	33	31	W

- Typical Class AB performance in Raytron DEMO with the device soldered onto the heatsink, test condition: V_{DS} = 28V, I_{DS} = 100mA, V_{GS} = -2.70V
- Test Condition: Pulse, Pulse width = 100μs, Duty cycle = 10%

5. Block Diagram



1. **Gate**
2. **Drain**
3. **Source**

D1320-PDS-F02

Figure 2. D1320 Block Diagram

Table of Contents

No.	Contents	Page
1	Description	1
2	Applications	1
3	Features	1
4	Brief Typical Performance	1
5	Block Diagram	1
6	Absolute Maximum Ratings	3
7	Recommended Operating Conditions	3
8	Electrical Characteristics	3
9	Wide-band Application Performance	4
10	Package Outline	6
11	Application Circuit	7
12	DEMO Summary	8
13	Recommended Solder Temperature Profile	8
14	Handling Precautions	9
15	Contact Information	9
16	Disclaimer	9

6. Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DSS}	84	V
Gate-Source Voltage	V_{GS}	-10 ~ +1	V
Operating Voltage	V_{DS}	10 ~ +32	V
Maximum Forward Gate Current	I_{GMax}	6.72	mA
Storage Temperature Range	T_{STG}	-65 ~ +150	°C
Operating Junction Temperature	T_J	250	°C

7. Recommended Operating Conditions

Table 3. Recommended Operating Conditions

Parameter	Min.	Typ.	Max.	Units
Drain-Source Voltage Range, V_{DS}	-	28	-	V
Drain Bias Current, I_{DS}	-	100	-	mA
Gate-Source Voltage, V_{GS}	-	-2.70	-	V
Channel Temperature, T_{CH}	-	-	225	°C

Table 4. Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance (Active Die Surface-to-Case)[1]	R_{thsc} (IR)	3.30	°C/W
Thermal Resistance (Junction-to-Case)[2]	R_{thjc} (FEA)	4.38	°C/W

[1]. Thermal Resistance at average power by infrared measurement, Active Die Surface-to-Case, $T_{base\text{-}plate}$ = 85℃, P_D = 23.0W

[2]. Thermal Resistance at average power by Finite Element Analysis, Junction-to-Case, $T_{base\text{-}plate}$ = 85℃, $T_{junction}$ = 200℃

8. Electrical Characteristics (T_C = 25˚C)

Table 5. DC Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage[1] (V_{GS} = -10V, I_{DS} = 6.72mA)	$V_{DS(BR)}$	84	-	-	V
Saturated Drain Current[2] (V_{DS} = 10V, V_{GS} = 1.0V)	I_{Max}	-	7.73	-	A
Gate Threshold Voltage[3] (V_{DS} = 28V, I_{DS} = 6.72mA)	$V_{GS(th)}$	-3.30	-2.80	-2.30	V
Gate Quiescent Voltage[3] (V_{DS} = 28V, I_{DS} = 100mA)	$V_{GS(Q)}$	-	-2.70	-	V

[1]. Measured on wafer prior to packaging

[2]. Measured with packaged device

[3]. Measured in Raytron DEMO

9. Wide-band Application Performance

■ Wide-band Application Performance (DEMO_A, 3.4-3.7GHz, Pulse)

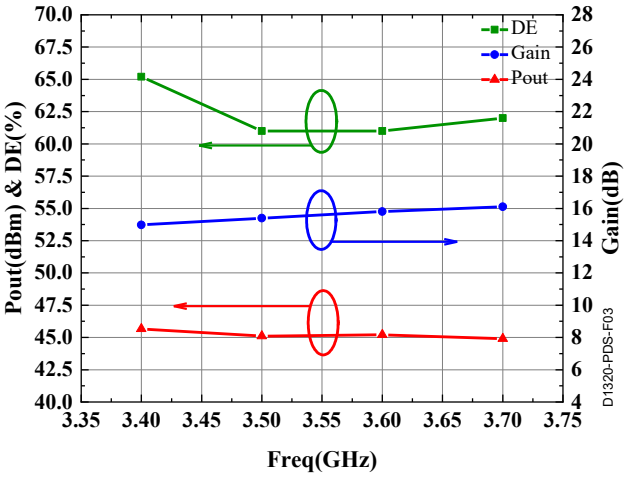


Figure 3. 3.4GHz-3.7GHz Gain and P_{out} vs. Freq.

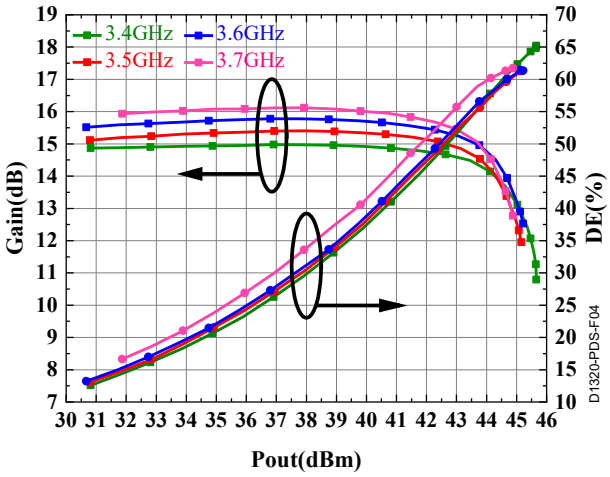


Figure 4. 3.4GHz-3.7GHz Gain and DE vs. Output Power

Table 6. RF Characteristics

Parameter	3.4GHz	3.5GHz	3.6GHz	3.7GHz	Units
Linear Gain	15.0	15.4	15.8	16.1	dB
Power Gain	12.1	12.3	12.5	12.8	dB
Drain Efficiency	65.0	61.0	61.0	62.0	%
Output Power	45.5	45.1	45.2	44.9	dBm
Output Power	35	32	33	31	W

- Typical Class AB performance in Raytron DEMO_A with the device soldered onto the heatsink, test condition: V_{DS} = 28V, I_{DS} = 100mA, V_{GS} = -2.70V
- Test Condition: Pulse, Pulse width = 100μs, Duty cycle = 10%
- The output power is 44.9dBm (31W) at 3.4-3.7GHz.

■ Wide-band Application Performance (DEMO_A, 3.4-3.7GHz, CW)

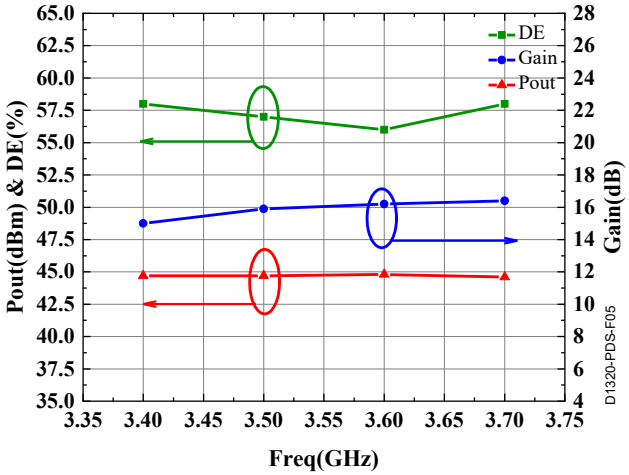


Figure 5. 3.4GHz-3.7GHz CW Gain and P_{out} vs. Freq.

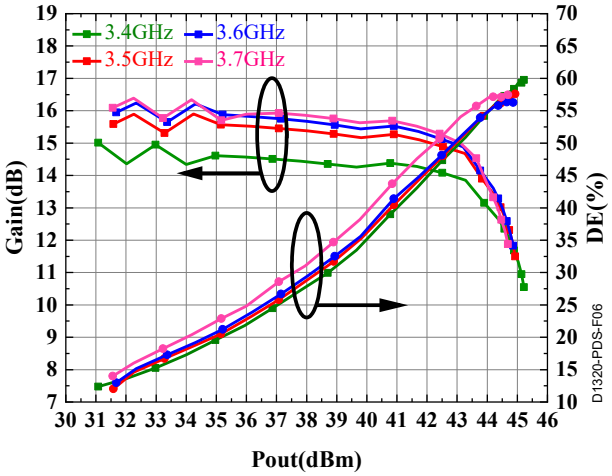


Figure 6. 3.4GHz-3.7GHz CW Gain and DE vs. Output Power

Table 7. RF Characteristics

Parameter	3.4GHz	3.5GHz	3.6GHz	3.7GHz	Units
Linear Gain	15.0	15.9	16.2	16.4	dB
Power Gain	12.0	12.3	12.2	12.3	dB
Drain Efficiency	58.0	57.0	56.0	58.0	%
Output Power	44.7	44.7	44.8	44.6	dBm
Output Power	30	30	30	29	W

- Typical Class AB performance in Raytron DEMO_A with the device soldered onto the heatsink, test condition: V_{DS} = 28V, I_{DS} = 100mA, V_{GS} = -2.70V
- Test Condition: CW
- The output power is 44.6dBm (29W) at 3.4-3.7GHz.

10. Package Outline

■ Pin Layout

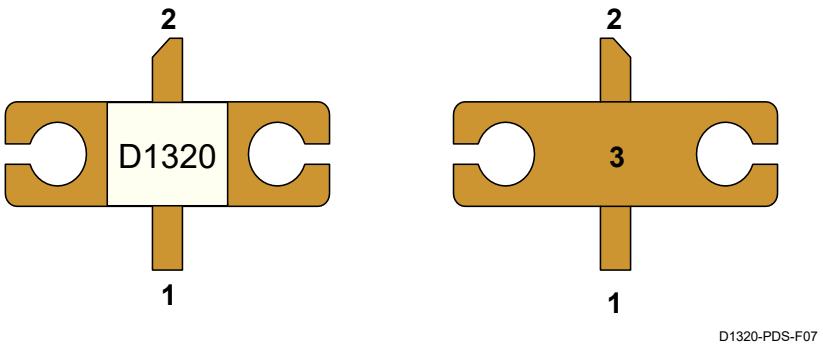


Figure 7. D1320 Pin Layout

Table 8. Pin Description

Pin	Symbol	Description
1	V_G / RF IN	Gate Voltage / RF Input
2	V_D / RF OUT	Drain Voltage / RF Output
3	Flange	Source to be Connected to Ground

■ Mechanical Drawing (Package Type:200F-A)

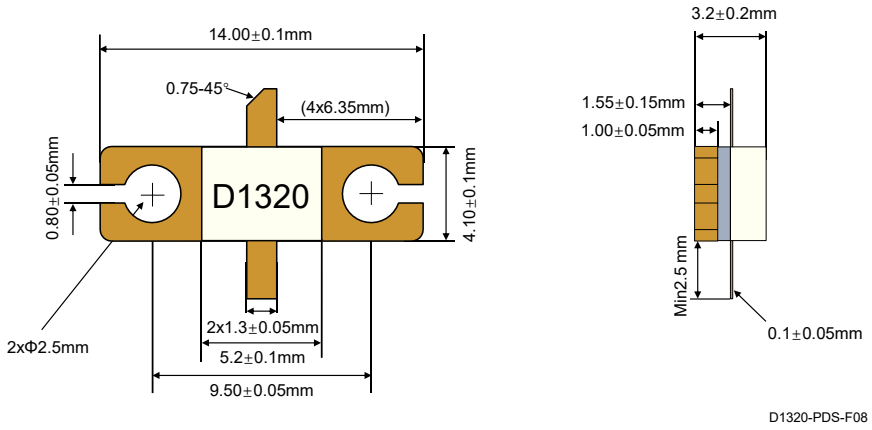


Figure 8. D1320 Mechanical Drawing

11. Application Circuit

■ Schematic

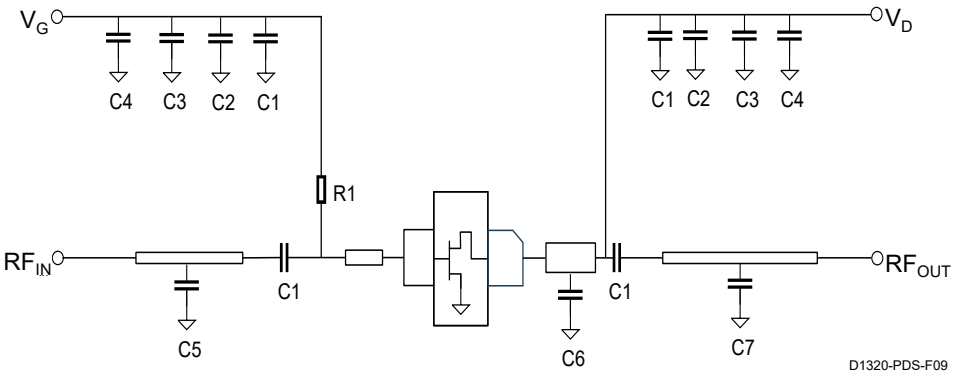


Figure 9. D1320 DEMO_A Application Circuit Schematic

Table 9. Bias Procedure

Bias-up Procedure	Bias-down Procedure
1) Set V_{GS} to the pinch-off voltage, typically -6V	1) Turn off RF signal
2) Turn on V_{DS} to nominal supply voltage (28V)	2) Turn off V_{DS}
3) Slowly adjust V_{GS} until I_{DS} current is attained	3) Wait two seconds to allow drain capacitor to discharge
4) Apply RF input power to desired level	4) Turn off V_{GS}

■ Layout

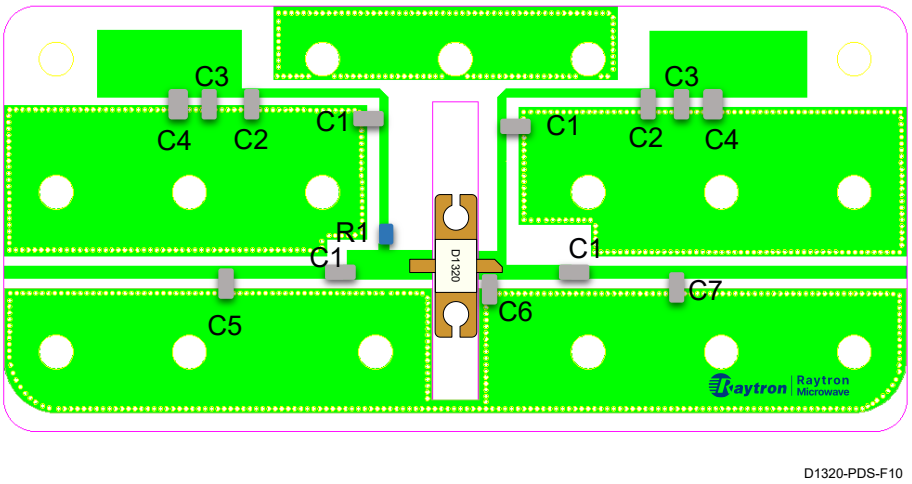


Figure 10. D1320 DEMO_A Application Circuit Layout（3.4GHz-3.7GHz）
（DEMO Size: 4.0cm x 8.5cm）

Table 10. Bill of Materials

Component	Value	Description	Manufacturer	Part Number
PCB	20mil	N/A	Rogers	RO4350B
C1	4.3pF	C0G 250V 0805 Capacitor	Murata	GQM2195C2E4R3BB12D
C2	100.0pF	C0G 250V 0805 Capacitor	Murata	GQM2195C2E101JB12D
C3	10.0nF	X7R 100V 0603 Capacitor	Murata	GCM188R72A103KA37D
C4	1.0uF	X7R 100V 1210 Capacitor	Murata	GRM32ER72A105KA01L
C5	0.3pF	C0G 250V 0805 Capacitor	Murata	GQM2195C2ER30WB12D
C6	0.9pF	C0G 250V 0805 Capacitor	Murata	GQM2195C2ER90WB12D
C7	0.5pF	C0G 250V 0805 Capacitor	Murata	GQM2195C2ER50WB12D
R1	10Ω	1/8W 0805 Resistor	Yageo	RC0805FR-0710RL

12. DEMO Summary

Table 11. DEMO Summary

NO.	D1320 DEMO Name	V_{DS} (V)	Freq (GHz)	Linear Gain(dB)	P_{SAT} (dBm)	P_{SAT} (W)	Drain Efficiency	Pulse or CW
1	DEMO_A, 30W	28	3.4-3.7	15.0	44.8	30	56%	CW

13. Recommended Solder Temperature Profile

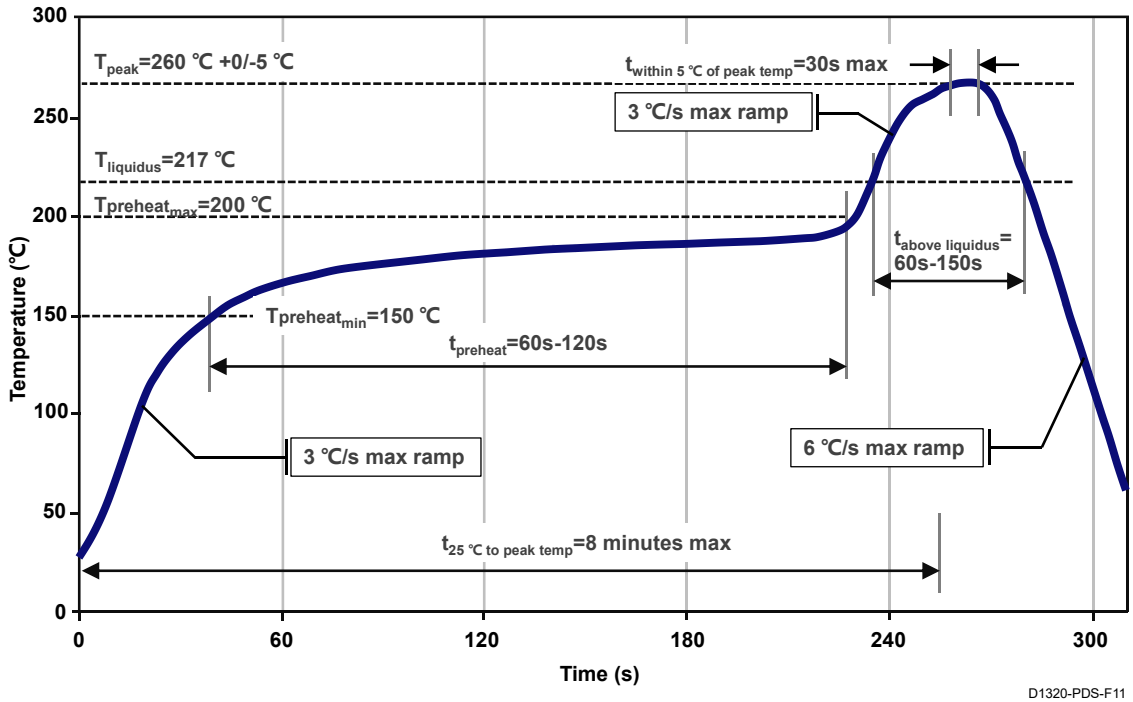


Figure 11. Recommended Solder Temperature Profile

14. Handling Precautions

- **ESD Caution**

  ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore proper ESD precautions should be taken to avoid performance degradation or loss of functionality.



15. Contact Information

For the latest specifications, additional product information, technical support and sales support, please contact:

- **Email:** RF.support@raytrontek.com
- **Web:** www.raytrontek.com

16. Disclaimer

The information provided here is believed to be reliable at the time of publication. Raytron reserves the right to make changes to its products, specifications and product descriptions at any time without notice. Raytron assumes no responsibility for the use of this information and all such information should entirely be at the user's own risk. Raytron makes no warranty about the suitability of its products for specific purpose or application and disclaims all liability, including without limitation consequential and incidental damages. Raytron does not authorize or warrant any Raytron products for use in the life support devices or systems.

Raytron Microwave

Copyright @ Raytron Technology Co., Ltd.